

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-13. (canceled)

14. (previously presented) A device comprising:

a silicon layer;
a relaxed layer; and

a strained silicon layer in contact with the relaxed layer, the strained silicon layer to be transferred to top of a wafer by a heat treatment, the wafer having a base substrate and an oxidized film.

15. (previously presented) The device of claim 14 further comprising an embrittled region.

16. (previously presented) The device of claim 15 wherein the embrittled region is created by an ion implantation.

17. (previously presented) A device comprising:

a silicon layer;
a SiO₂ layer in contact with the silicon layer; and
a strained silicon layer on top of the SiO₂ layer, the strained silicon layer being transferred from a wafer, the wafer having a stack structure of a base substrate and a layer of relaxed film.

18. (previously presented) The device of claim 17 wherein the relaxed film is a relaxed SiGe layer.

19. (previously presented) The device of claim 18 wherein the wafer further comprises an embrittled region.

20. (previously presented) The device of claim 17 wherein the strained silicon layer is transferred to top of the SiO₂ layer by a bonded-etch back process.

21. (previously presented) The device of claim 17 wherein the base substrate is a silicon layer.

22. (previously presented) The device of claim 17 wherein the heat treatment uses a temperature range of approximately 400°C to 600°C.

23. (previously presented) The device of claim 14 wherein the relaxed layer is a relaxed SiGe layer.

24. (previously added) The device of claim 23 wherein the relaxed SiGe layer has a thickness ranging from 0.1um to 3.0um.

25. (previously presented) The device of claim 16 wherein the ion implantation uses an energy range of approximately 1keV to 20keV.

26. (previously presented) The device of claim 16 wherein the ion implantation uses a dose range of approximately 1E116/cm³ to 1E18/cm³.

27. (previously presented) The device of claim 16 wherein the ion implantation uses hydrogen ions.

28-33 (canceled)